

2SA1737

Silicon PNP epitaxial planer type

For video amplifier

Features

- High transition frequency f_T .
- Small collector output capacitance C_{ob} .
- Mini Power type package, allowing downsizing of the equipment and automatic insertion through the tape packing and the magazine packing.

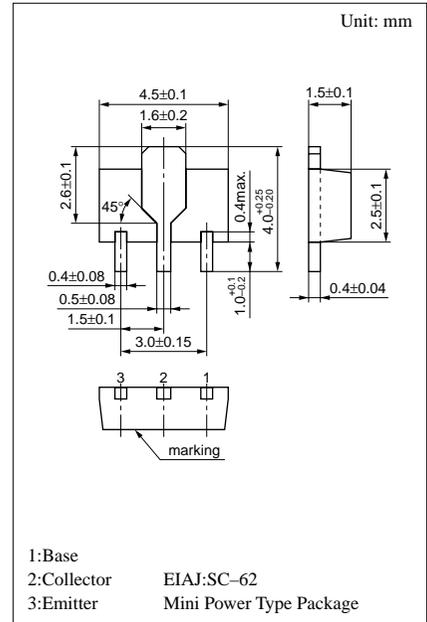
Absolute Maximum Ratings (Ta=25°C)

Parameter	Symbol	Ratings	Unit
Collector to base voltage	V_{CBO}	-85	V
Collector to emitter voltage	V_{CEO}	-85	V
Emitter to base voltage	V_{EBO}	-4	V
Peak collector current	I_{CP}	-100	mA
Collector current	I_C	-50	mA
Collector power dissipation	P_C^*	1	W
Junction temperature	T_j	150	°C
Storage temperature	T_{stg}	-55 ~ +150	°C

* Printed circuit board: Copper foil area of 1cm² or more, and the board thickness of 1.7mm for the collector portion

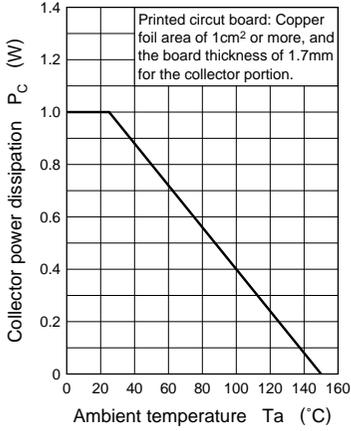
Electrical Characteristics (Ta=25°C)

Parameter	Symbol	Conditions	min	typ	max	Unit
Collector cutoff current	I_{CEO}	$V_{CE} = -60V, I_B = 0$			-10	μA
Collector to base voltage	V_{CBO}	$I_C = -100\mu A, I_E = 0$	-85			V
Collector to emitter voltage	V_{CEO}	$I_C = -1mA, I_B = 0$	-85			V
Emitter to base voltage	V_{EBO}	$I_E = -100\mu A, I_C = 0$	-4			V
Forward current transfer ratio	h_{FE}	$V_{CE} = -5V, I_C = -10mA$	60			
Collector to emitter saturation voltage	$V_{CE(sat)}$	$I_C = -10mA, I_B = -1mA$			-0.5	V
Transition frequency	f_T	$V_{CB} = -5V, I_E = 10mA, f = 200MHz$		500		MHz
Collector output capacitance	C_{ob}	$V_{CB} = -10V, I_E = 0, f = 1MHz$		2.7		pF

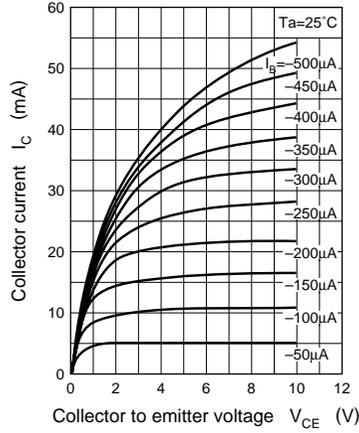


Marking symbol : 1E

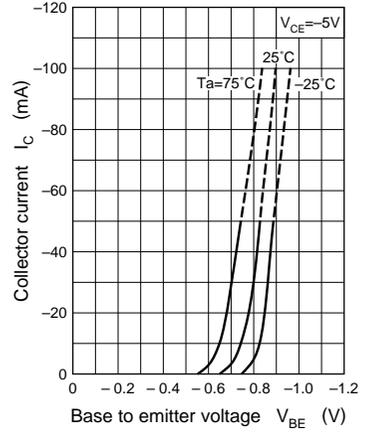
$P_C - T_a$



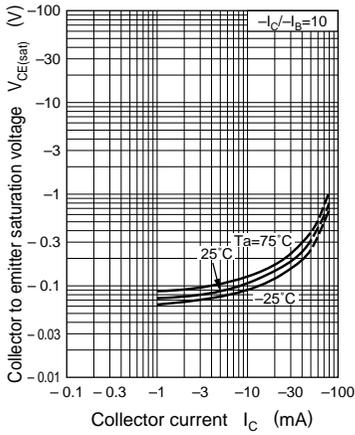
$I_C - V_{CE}$



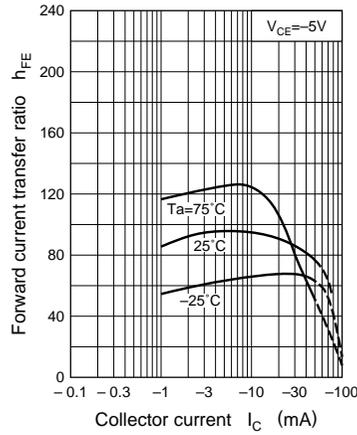
$I_C - V_{BE}$



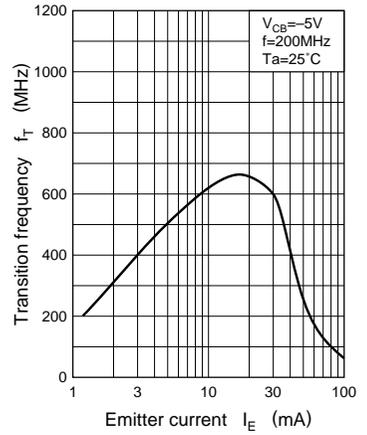
$V_{CE(sat)} - I_C$



$h_{FE} - I_C$



$f_T - I_E$



$C_{ob} - V_{CB}$

